

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|---------|--|---|------------------|---------|------------------|
| | | ((via near hole) or via) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal and "257".cls. | US-PGPUB; USPAT | OR | ON | 2005/11/25 17:36 |
| L1 | 172341 | substrate and gate | US-PGPUB; USPAT; USOCR | OR | ON | 2006/05/18 14:03 |
| L2 | 281549 | substrate and gate | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/18 14:04 |
| L3 | 57638 | interlayer\$2 near (dielectric or insulat\$3) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/18 14:04 |
| L4 | 8404268 | vias or (via near hole\$1) or (contact hole\$1) or (contact near plug\$1) or (conductive near plug\$1) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/18 14:05 |
| L5 | 447621 | l4 same (taper\$3 or slop\$3 or slant\$3) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/18 14:05 |
| L6 | 122028 | (arc or antireflect\$) and (silicon or si) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/18 14:06 |
| L7 | 133 | l2 and l3 and l5 and l6 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/18 15:06 |

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| L8 | 0 | (trench or groove) with (tapered tapering taper) with conformal with polysilicon | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/18 15:07 |
| L9 | 52 | (trench or groove) with (tapered tapering taper) with polysilicon | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/18 15:09 |
| L10 | 43 | (trench or groove) with (tapered tapering taper) with polysilicon | US-PGPUB; USPAT | OR | ON | 2006/05/18 15:14 |
| L11 | 30 | l10 not dram | US-PGPUB; USPAT | OR | ON | 2006/05/18 15:14 |
| L12 | 4 | (trench or groove) with (tapered tapering taper) with polysilicon with void | US-PGPUB; USPAT | OR | ON | 2006/05/18 15:16 |
| L13 | 0 | (contact or hole) with (tapered tapering taper) with polysilicon with void | US-PGPUB; USPAT | OR | ON | 2006/05/18 15:16 |
| L14 | 3 | (sidewall) with (tapered tapering taper) with polysilicon with void | US-PGPUB; USPAT | OR | ON | 2006/05/18 15:20 |
| L15 | 38 | (contact) with (tapered tapering taper) with polysilicon | US-PGPUB; USPAT | OR | ON | 2006/05/18 15:20 |
| S1 | 2 | ("20050085086").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/17 12:51 |
| S2 | 1052 | 257/734.ccls. | US-PGPUB; USPAT | OR | ON | 2005/11/25 15:57 |
| S3 | 811 | S2 and @ad<="20031021" | US-PGPUB; USPAT | OR | ON | 2005/11/25 16:59 |
| S4 | 453 | S3 and via | US-PGPUB; USPAT | OR | ON | 2005/11/25 17:26 |
| S5 | 100 | S3 and via and gate | US-PGPUB; USPAT | OR | ON | 2005/11/25 17:28 |
| S6 | 6682 | via near hole and gate | US-PGPUB; USPAT | OR | ON | 2005/11/25 17:29 |
| S7 | 3528 | via near hole and gate and semiconductor near device | US-PGPUB; USPAT | OR | ON | 2005/11/25 17:30 |

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|-----|-------|---|---|----|-----|------------------|
| S8 | 0 | via near hole and gate and semiconductor near device and silicon near layer and substrate and dielectric and metal | US-PGPUB; USPAT | OR | ON | 2005/11/25 17:30 |
| S9 | 20751 | ((via near hole) or via) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal | US-PGPUB; USPAT | OR | ON | 2005/11/25 17:36 |
| S10 | 14801 | ((via near hole) or via) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal and "257".clas. | US-PGPUB; USPAT | OR | ON | 2005/11/25 17:37 |
| S11 | 13023 | ((via near hole) or via) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal and "257".clas. and @ad<="20031021" | US-PGPUB; USPAT | OR | ON | 2005/11/25 17:37 |
| S12 | 1892 | (via near hole) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal and "257".clas. and @ad<="20031021" | US-PGPUB; USPAT | OR | ON | 2005/11/25 17:37 |
| S13 | 1 | ("6791187").PN. | US-PGPUB; USPAT | OR | OFF | 2005/11/28 13:19 |
| S14 | 0 | ("1761481986").PN. | US-PGPUB; USPAT; JPO | OR | OFF | 2005/11/28 13:19 |
| S15 | 2 | ("0176148").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/11/28 13:20 |
| S16 | 0 | (176148/1986).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/11/28 13:20 |
| S17 | 0 | ("1761481986").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/11/28 13:20 |

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| S18 | 0 | "1761481986" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/28 13:21 |
| S19 | 7 | 176148/1986 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/28 13:47 |
| S20 | 100 | tapered near via near hole | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/28 13:47 |
| S21 | 62 | tapered near via near hole | US-PGPUB; USPAT | OR | ON | 2005/11/28 13:50 |
| S22 | 7 | tapered near via near hole and anisotropically | US-PGPUB; USPAT | OR | ON | 2005/11/28 16:20 |
| S23 | 3742 | 257/774 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/28 16:21 |
| S24 | 3108 | 257/773 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/28 16:21 |
| S25 | 1948 | 257/734 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/28 16:22 |
| S26 | 585 | 257/770 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/28 16:24 |

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|-----|------|---|---|----|-----|------------------|
| S27 | 1819 | 257/750 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/28 16:24 |
| S28 | 5222 | 257/758 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/28 16:24 |
| S29 | 1363 | 257/763 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/28 16:24 |
| S30 | 2395 | 438/706 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/28 16:24 |
| S31 | 2 | ("6791187").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/17 12:51 |
| S32 | 28 | ("4840923" "4974040" "5036370" "5061985" "5150276" "5150278" "5196910" "5204286" "5281549" "5292677" "5302551" "5324681" "5346844" "5389568" "5414655" "5479054" "5561311" "5573965" "5605857" "5612254" "5623164" "5661344" "5689126" "5732009" "5760429" "5793076" "5874756" "6150689").PN. OR ("6791187"). URPN. | US-PGPUB; USPAT; USOCR | OR | ON | 2006/05/17 14:11 |
| S33 | 39 | ("4649406" "4700457" "4742018").PN. OR ("4974040"). URPN. | US-PGPUB; USPAT; USOCR | OR | ON | 2006/05/17 15:10 |
| S34 | 0 | S32 and S33 and (taper tapered) and gate and silicon and etch | US-PGPUB; USPAT; USOCR | OR | ON | 2006/05/17 15:11 |

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|-----|------|---|------------------------------|----|----|------------------|
| S35 | 0 | S32 and S33 and (taper tapered) and gate and silicon and (etch etching) | US-PGPUB; USPAT; USOCR | OR | ON | 2006/05/17 15:11 |
| S36 | 0 | S32 and S33 and (taper tapered) | US-PGPUB; USPAT; USOCR | OR | ON | 2006/05/17 15:11 |
| S37 | 2008 | (taper tapered) and gate and (etch and etching) and hole and via | US-PGPUB; USPAT; USOCR | OR | ON | 2006/05/17 15:11 |
| S38 | 1911 | (taper tapered) and gate and (etch and etching) and hole and via and silicon | US-PGPUB; USPAT; USOCR | OR | ON | 2006/05/17 15:12 |
| S39 | 1911 | (taper tapered) and gate and (etch and etching) and hole and via and silicon and (antireflective silicon dioxide oxide) | US-PGPUB; USPAT; USOCR | OR | ON | 2006/05/18 14:03 |